

MCK-005.25-US

**Appendix A  
In the Claims:**

1. (canceled)
2. (canceled)
3. (canceled)
4. (canceled)
5. (canceled)
6. (canceled)
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8. (canceled)
9. (canceled)
10. (canceled)
11. (canceled)
12. (canceled)
13. (canceled)
14. (canceled)
15. (canceled)
16. (canceled)
17. (canceled)
18. (canceled)
19. (canceled)
20. (previously added) A method of making a dielectric layer between a pair of opposing electrodes comprising the steps of:  
forming, as said dielectric layer, an epitaxial thin film on a textured substrate;  
forming one of said electrodes on an exposed surface of said thin film;  
wholly or partially removing said textured substrate; and  
forming an electrical connection to access said dielectric layer on the side of said textured substrate.
21. (previously added) The method according to Claim 20 wherein the textured substrate comprises nickel.
22. (previously added) The method according to Claim 22 wherein said epitaxial thin film is formed from perovskite.
23. (New) The method of claim 20, wherein said thin film is formed of a ferroelectric material.
24. (New) The method of claim 20, wherein said epitaxial thin film comprises substantially a single crystal.
25. (New) The method of claim 20, wherein at least one of said electrodes is formed by being directly deposited on the surface of said thin film.

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26. (New) The method of claim 20, wherein the dielectric has high permittivity.
27. (New) The method of claim 20, wherein an insulator is formed onto parts of the side of the textured substrate.
28. (New) The method of claim 20, further comprising the step of embedding the dielectric layer within a printed wiring board.
29. (New) The method of claim 20, further comprising the step of forming the dielectric layer as part of a discrete capacitor.
30. (New) The method of claim 20, further comprising forming the dielectric layer as part of a tunable filter.
31. (New) The method of claim 20, further comprising forming the dielectric layer as part of a phase shifter.
32. (New) The method of claim 20, wherein the dielectric is barium strontium titanate.
33. (New) The method of claim 20, wherein the dielectric can transmit oxygen.
34. (New) The method of claim 20, wherein the dielectric is a zirconate or cerate.
35. (New) The method of claim 20, wherein at least one electrode is a conductive oxide.
36. (New) The method of claim 20, wherein at least one electrode is a cermet.

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## Appendix B

<u>Claim</u>	<u>Recitation</u>	<u>In Application</u>	<u>In Publication</u> (paragraph)
23	ferroelectric	Page 11, line 2	26
24	Single Crystal thin film	Page 17, line 10	52
25	Electrode directly deposited on thin film	Page 15, lines 23-24	48
26	High Permittivity	Page 11, line 2	26
27 DROP	DROP	DROP	DROP
28 (change)	Embedding (capacitor)	Page 10, line 29, Page 11, line 6	25 26
29	Discrete capacitor	Page 10, lines 28-29	25
30	Tunable Filter	Page 11, lines 8-10	26
31	Phase Shifter	Page 11, lines 7-8	26
32	Barium Strontium Titanate	Page 21, line 20	63
33	Dielectric transmits oxygen	Page 17, line 19, Page 24, line 9	52 Abstract
34	Zirconate, cerate	Page 10, lines 9-10	23
35 DROP	DROP	DROP	DROP
36	Electrode a cermet	Page 18, line 21	51

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